

# MA4X796

## Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

### ■ Features

- Two MA3X787s in the same direction are contained in one package
- Allowing to rectify under ( $I_{F(AV)} = 100$  mA) condition
- Optimum for high-frequency rectification because of its short reverse recovery time ( $t_{rr}$ )
- Low  $V_F$  (forward rise voltage), with high rectification efficiency
- Reverse voltage  $V_R$  (DC value) = 50 V guaranteed

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	50	V
Repetitive peak reverse voltage	$V_{RRM}$	50	V
Peak forward current	Single	$I_{FM}$	300
	Double*2		200
Average forward current	Single	$I_{F(AV)}$	100
	Double*2		70
Non-repetitive peak forward surge current*1	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \*1: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

\*2: Value per chip

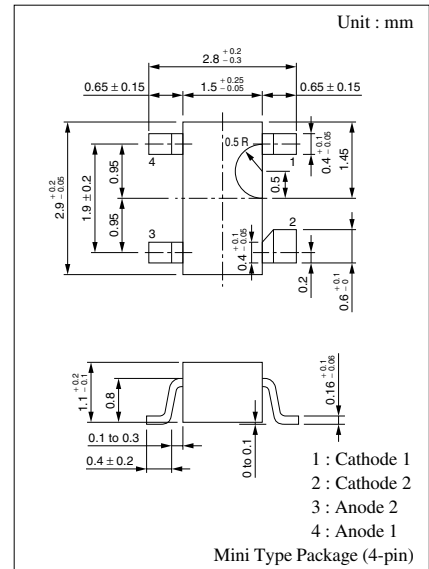
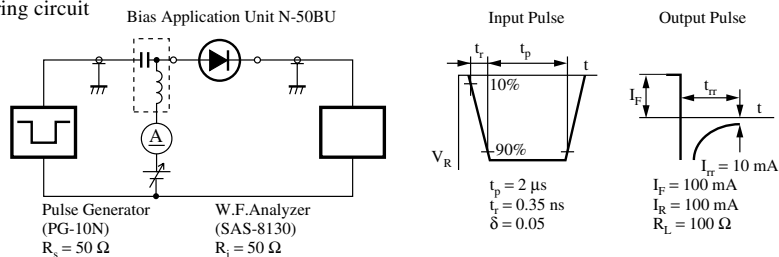
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 50$ V			30	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 100$ mA			0.55	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		25		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA $I_{rr} = 10$ mA, $R_L = 100$ $\Omega$		3		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 200 MHz

3. \*:  $t_{rr}$  measuring circuit



Marking Symbol: M4B

Internal Connection

